



5MHz to 4000MHz LOW NOISE MMIC AMPLIFIER SILICON GERMANIUM

Package: QFN, 2x2



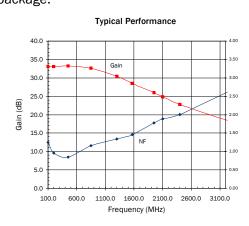


Product Description

The SGL0622Z is a low noise, high gain MMIC LNA designed for low power single-supply operation from 2.7V to 3.6V. Its Class-1C ESD protection and high input overdrive capability ensures rugged performance, while its integrated active bias circuit maintains robust stable bias over temperature and process beta variation. The SGL0622Z is internally matched from 5MHz to 4000 MHz and requires only 4 to 5 external biasing components (DC blocks, bypass caps, inductive choke). The SGL0622Z is fabricated using highly repeatable Silicon Germanium technology and is housed in a

cost-effective RoHS/WEEE compliant QFN 2x2 miniature package.





Features

- High Gain=28dB at 1575MHz
- Low Noise Figure = 1.5dB at 1575MHz
- Low Power Consumption, 10.5 mA @ 3.3 V
- Battery Operation: 2.7 V to 3.6 V (Active Biased)
- Fully Integrated Matching
- Class-1C ESD Protection (>1000V HBM)
- High input overdrive capability, +18dBm

Applications

- High Gain GPS Receivers
- ISM and WiMAX LNAs

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Parameter	Min.	Тур.	Max.	Unit	Condition		
Small Signal Gain	25.0	28.0	31.0	dB	1.575GHz		
		23.0		dB	2.44GHz		
	14.5	16.5	18.5	dB	3.50 GHz		
Output Power at 1dB Compression	3.3	5.3		dBm	1.575 GHz		
		1.5		dBm	2.44GHz		
		-1.4		dBm	3.50GHz		
Input Third Order Intercept Point	-16.0	-13.0		dBm	1.575 GHz		
		-12.0		dBm	2.44GHz		
		-8.5		dBm	3.50GHz		
Input Return Loss	12.0	14.0		dB	1.575 GHz		
		12.0		dB	2.44GHz		
		10.0		dB	3.50GHz		
Output Return Loss	6.0	9.5		dB	1.575 GHz		
		14.0		dB	2.44GHz		
		22.0		dB	3.50GHz		
Noise Figure		1.5	1.9	dB	1.575 GHz		
		2.0		dB	2.44GHz		
		2.8		dB	3.50GHz		
Reverse Isolation		-28.0		dB	0.05 GHz to 4.0 GHz		
Thermal Resistance		150		°C/W	junction - lead		
Device Operating Current	7.5	10.5	12.5	mA			

Test Conditions: V_{CC} =3.3V, I_D =10.5mA Typ., IIP₃ Tone Spacing=1MHz, P_{OUT} per tone=-15dBm, T_L =25°C, Z_S = Z_L =50 Ω

SGL0622Z



Absolute Maximum Ratings

Parameter	Rating	Unit
Device Current (I _D)	20	mA
Device Voltage (V _D)	4	V
RF Input Power* (See Note)	18	dBm
Junction Temp (T _J)	+150	°C
Operating Temp Range (T _L)	-40 to +85	°C
Storage Temp	+150	°C
ESD Rating - Human Body Model (HBM)	Class 1C	
Moisture Sensitivity Level	MSL 1	

^{*}Note: Load condition1, $ZL=50\Omega$. Load condition2, $Z_1=10:1$ VSWR.

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

 $I_DV_D < (T_J - T_L) / R_{TH}$, j-I and $T_L = T_{LEAD}$



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

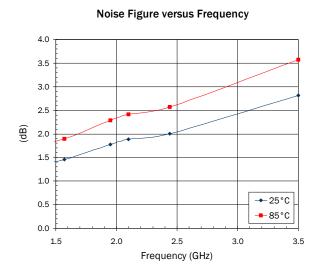
Typical RF Performance at Key Operating Frequencies (WIth Application Circuit)

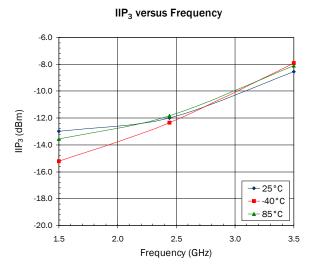
Parameter	Unit	100	200	450	850	1575	1950	2440	3550
		MHz	MHz	MHz	MHz	MHz	MHz	MHz	MHz
Small Signal Gain, S21	dB	34.6	34.9	34.4	32.8	28.5	26.1	23.0	17.0
Input Third Order Intercept Point, IIP3	dBm					-13.0		-12.0	-8.5
Output at 1dB Compression, P1dB	dBm	2.7				5.3		1.5	-1.4
Input Return Loss	dB	15.1	20.0	12.6	16.0	14.3	12.8	12.0	10.0
Output Return Loss	dB	9.2	12.2	11.8	10.4	9.5	12.1	14.0	22.0
Reverse Isolation	dB	38.8	39.8	38.7	39.9	35.6	34.8	32.0	29.0
Noise Figure, NF	dB	1.25	0.96	0.84	1.16	1.50	1.78	2.01	2.81

Test Conditions: V_{CC} =3.3V I_D =10.5 mA Typ. IIP $_3$ Tone Spacing=1MHz, P_{OUT} per tone=-15 dBm T_L =25 °C Z_S = Z_L =50 Ω

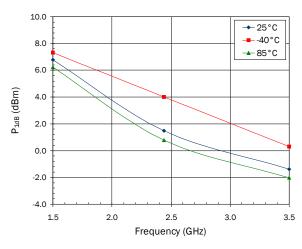








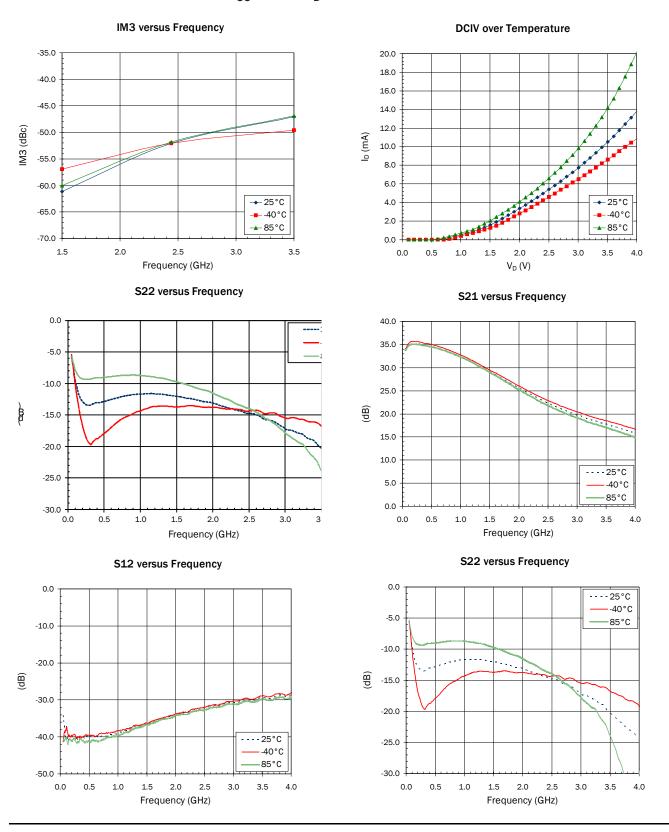
P_{1dB} versus Frequency



SGL0622Z



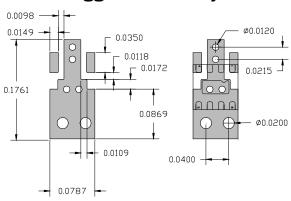
Application Circuit Data, V_{cc} = 3.3V, I_{D} = 9mA





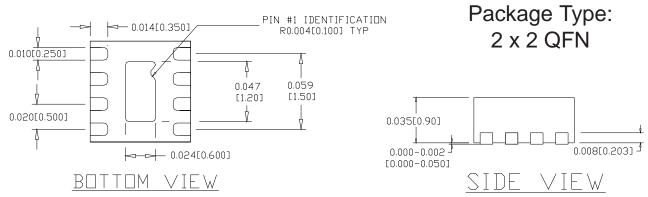
Pin	Function	Description
1	RF OUT/VD	RF output and bias pin. Bias should be supplied to this pin through an external RF choke. (See application circuit)
2	GND	Connect to ground per application circuit drawing.
3, 5,	N/A	Not Used
6, 7, 8		
4	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor as shown in the application schematics.
EPAD	GND	Exposed area on the bottom side of the package needs to be soldered to the ground plane of the board for thermal and RF performance. Vias should be located under the EPAD as shown in the recommended land pattern.

Suggested Pad Layout

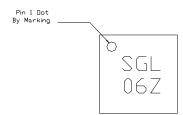


Nominal Package Dimensions

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.

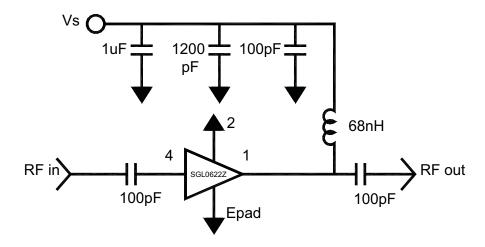


Part Identification

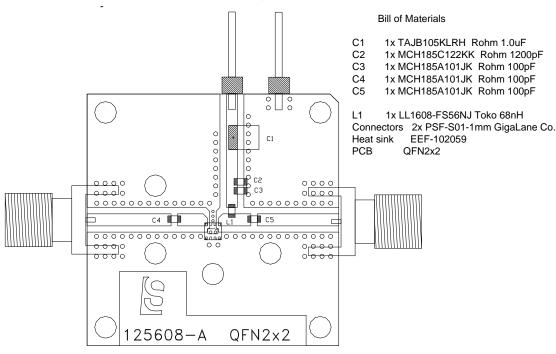




Application Schematic



Evaluation Board Layout and Bill of Materials



Ordering Information

Part Number	Description		
SGL0622Z	7" Reel with 3000 pieces		
SGL0622ZSQ	Sample Bag with 25 pieces		
SGL0622ZSR	7" Reel with 100 pieces		
SGL0622ZPCK1	100MHz to 3500MHz PCBA with 5-piece Sample Bag		